

30

**TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT**  
(Under 37 CFR 1.97(b) or 1.97(c))

Docket No.  
SEC.798

In Re Application Of: **Kyoung-sub SHIN et al.**

DEC 19 2003

Serial No.  
09/847,289

Filing Date  
May 3, 2001

Examiner  
To Be Assigned

Group Art Unit  
1765 ✓

Title: **METHOD OF FORMING A SELF-ALIGNED CONTACT, AND METHOD OF FABRICATING A SEMICONDUCTOR DEVICE HAVING A SELF-ALIGNED CONTACT**

Address to:  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**37 CFR 1.97(b)**

1. ☒ The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application other than a continued prosecution application under 37 CFR 1.53(d); within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; before the mailing of a first Office Action on the merits, or before the mailing of a first Office Action after the filing of a request for continued examination under 37 CFR 1.114.

**37 CFR 1.97(c)**

2. ☐ The Information Disclosure Statement submitted herewith is being filed after the period specified in 37 CFR 1.97(b), provided that the Information Disclosure Statement is filed before the mailing date of a Final Action under 37 CFR 1.113, a Notice of Allowance under 37 CFR 1.311, or an Action that otherwise closes prosecution in the application, and is accompanied by one of:

☐ the statement specified in 37 CFR 1.97(e);

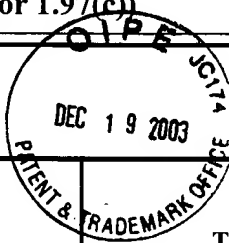
**OR**

☐ the fee set forth in 37 CFR 1.17(p).

**TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT**  
(Under 37 CFR 1.97(b) or 1.97(c))

Docket No.  
SEC.798

In Re Application: **Kyoung-sub SHIN et al.**



Serial No.  
09/847,289

Filing Date  
May 3, 2001

Examiner  
To Be Assigned

Group Art Unit  
1765

**METHOD OF FORMING A SELF-ALIGNED CONTACT, AND METHOD OF FABRICATING A SEMICONDUCTOR DEVICE HAVING A SELF-ALIGNED CONTACT**

**Payment of Fee**

(Only complete if Applicant elects to pay the fee set forth in 37 CFR 1.17(p))

- ☐ A check in the amount of \_\_\_\_\_ is attached.
- ☐ The Director is hereby authorized to charge and credit Deposit Account No. \_\_\_\_\_ as described below.
- ☐ Charge the amount of \_\_\_\_\_
- ☐ Credit any overpayment.
- ☐ Charge any additional fee required.

**Certificate of Transmission by Facsimile\***

I certify that this document and authorization to charge deposit account is being facsimile transmitted to the United States Patent and Trademark Office (F:

\_\_\_\_\_  
(Date)

\_\_\_\_\_  
Signature

\_\_\_\_\_  
Typed or Printed Name of Person Signing Certificate

**Certificate of Mailing by First Class Mail**

I certify that this document and fee is being deposited on \_\_\_\_\_ with the U.S. Postal Service as first class mail under 37 C.F.R. 1.8 and is addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

\_\_\_\_\_  
Signature of Person Mailing Correspondence

\_\_\_\_\_  
Typed or Printed Name of Person Mailing Certificate

\*This certificate may only be used if paying by deposit account.

  
Signature

Dated: **DECEMBER 19, 2003**

**ADAM C. VOLENTINE**  
REG. NO. 33,289

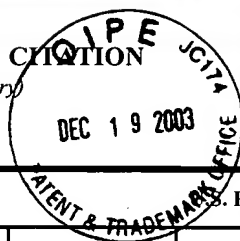
**VOLENTINE FRANCO, P.L.L.C.**  
12200 SUNRISE VALLEY DRIVE, SUITE 150  
RESTON, VA 20191

TEL. NO.: (703) 715-0870

CC:

# INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)



Docket Number (Optional)

SEC.798

Application Number

09/847,289

Applicant(s)

Kyoung-sub SHIN et al.

Filing Date

May 3, 2001

Group Art Unit

1765

## PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	A	6,136,643	10/24/2000	JENG et al.			
	B	6,150,281	11/21/2000	KWEAN			
	C	6,344,692	02/05/2002	IKEMASU et al.			
	D	2001/0034135 A1	10/25/2001	MIYAKAWA			
	E	6,197,670	03/06/2001	PARK			

## FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
	F	GB 2 333 179 A	07/14/1999	UK			✓	
	G	2000021985 A	01/21/2000	JAPAN			✓ Abstract only	
	H	10041482 A	02/13/1998	JAPAN			✓ Abstract only	
	I	2000040691 A	08/02/2000	JAPAN			✓ Abstract only	
	J	2000058482 A	02/25/2000	JAPAN			✓ Abstract only	

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	K	Y. Kohyama et al., "A Fully Printable, Self-aligned and Planarized Stacked Capacitor DRAM Cell Technology for 1Gbit DRAM and Beyond", 1997 Symposium on VLSI Technology Digest of Technical Papers, pgs. 17 & 18.

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.